

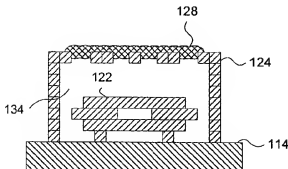
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- (71) Applicant: MEMGEN CORPORATION [US/US]; 1103 W. Isabel Street, Burbank, CA 91506 (US).
- (72) Inventors: COHEN, Adam, L.; 9537 Kirkside Road, Los Angeles, CA 90035 (US). LOCKARD, Michael, S.; 15152 Bluffon Street, Lake Elizabeth, CA 93532 (US). SMALLEY, Dennis, R.; 23524 Maple Street, Newhall, CA 91321 (US). ARAT, Vacit; 4093 Robin Hill Road, La Canada Flintridge, CA 91011 (US). LEE, Christopher, J.; 18555 Burbank Blvd., #25, Tarzana, CA 91356 (US).
- (74) Agent: SMALLEY, Dennis, R.; MEMGen Corp., 1103 W. Isabel Street, Burbank, CA 91506 (US).
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(54) Title: ELECTROCHEMICALLY FABRICATED HERMETICALLY SEALED MICROSTRUCTURES AND METHODS OF AND APPARATUS FOR PRODUCING SUCH STRUCTURES



(57) Abstract: In some embodiments, multilayer structures are electrochemically fabricated from at least one structural material (e.g. nickel), at least one sacrificial material (e.g. copper), and at least one sealing material (e.g. solder). In some embodiments, the layered structure is made to have a desired configuration which is at least partially and immediately surrounded by sacrificial material which is in turn surrounded almost entirely by structural material.

structural material includes openings in the surface through which etchant can attack and remove trapped sacrificial material found within. Sealing material is located near the openings. After removal of the sacrificial material, the box is evacuated or filled with a desired gas or liquid. Thereafter, the sealing material is made to flow, seal the openings, and resolidify. In other embodiments, a post-layer formation lid or other enclosure completing structure is added.

Related Applications

This application claims benefit of U.S. Provisional Patent Application Nos. 60/379,182, filed on May 7, 2002, and 60/430,809, filed December 2, 2002 both of which are incorporated herein by reference as if set forth in full.

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Field of the Invention

The present invention relates generally to the field of electrochemical fabrication and the associated formation of three-dimensional structures via a layer-by-layer build up of deposited materials. In particular, it relates to the formation of microstructures and the concurrent formation of packaging for such structures, such that for example, sacrificial material(s) are removed from internal cavities of the package and critical portions of the structure are sealed within the cavities.

Background of the Invention:

A technique for forming three-dimensional structures (e.g. parts, components, devices, and the like) from a plurality of adhered layers was invented by Adam L. Cohen and is known as Electrochemical Fabrication. It is being commercially pursued by MEMGen® Corporation of Burbank, California under the name EFAB™. This technique was described in US Patent No. 6,027,630, issued on February 22, 2000. This electrochemical deposition technique allows the selective deposition of a material using a unique masking technique that involves the use of a mask that includes patterned conformable material on a support structure that is independent of the substrate onto which plating will occur. When desiring to perform an electrodeposition using the mask, the conformable portion of the mask is brought into contact with a substrate while in the presence of a plating solution such that the contact of the conformable portion of the mask to the substrate inhibits deposition at selected locations. For convenience, these masks might be generically called conformable contact masks; the masking technique may be generically called a conformable contact mask plating process. More specifically, in the terminology of MEMGen® Corporation of Burbank, California such masks have come to be known as INSTANT MASKS™ and the process known as INSTANT MASKING™ or INSTANT MASK™ plating. Selective depositions using conformable contact mask plating may be used to form single layers of material or may be used to form multi-

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layer structures. The teachings of the '630 patent are hereby incorporated herein by reference as if set forth in full herein. Since the filing of the patent application that led to the above noted patent, various papers about conformable contact mask plating (i.e. INSTANT MASKING) and electrochemical fabrication have been published:

1. A. Cohen, G. Zhang, F. Tseng, F. Mansfeld, U. Frodis and P. Will, "EFAB: Batch production of functional, fully-dense metal parts with micro-scale features", Proc. 9th Solid Freeform Fabrication, The University of Texas at Austin, p161, Aug. 1998.
2. A. Cohen, G. Zhang, F. Tseng, F. Mansfeld, U. Frodis and P. Will, "EFAB: Rapid, Low-Cost Desktop Micromachining of High Aspect Ratio True 3-D MEMS", Proc. 12th IEEE Micro Electro Mechanical Systems Workshop, IEEE, p244, Jan 1999.
3. A. Cohen, "3-D Micromachining by Electrochemical Fabrication", Micromachine Devices, March 1999.
4. G. Zhang, A. Cohen, U. Frodis, F. Tseng, F. Mansfeld, and P. Will, "EFAB: Rapid Desktop Manufacturing of True 3-D Microstructures", Proc. 2nd International Conference on Integrated MicroNanotechnology for Space Applications, The Aerospace Co., Apr. 1999.
5. F. Tseng, U. Frodis, G. Zhang, A. Cohen, F. Mansfeld, and P. Will, "EFAB: High Aspect Ratio, Arbitrary 3-D Metal Microstructures using a Low-Cost Automated Batch Process", 3rd International Workshop on High Aspect Ratio MicroStructure Technology (HARMST'99), June 1999.
6. A. Cohen, U. Frodis, F. Tseng, G. Zhang, F. Mansfeld, and P. Will, "EFAB: Low-Cost, Automated Electrochemical Batch Fabrication of Arbitrary 3-D Microstructures", Micromachining and Microfabrication Process Technology, SPIE 1999 Symposium on Micromachining and Microfabrication, September 1999.
7. F. Tseng, G. Zhang, U. Frodis, A. Cohen, F. Mansfeld, and P. Will, "EFAB: High Aspect Ratio, Arbitrary 3-D Metal Microstructures using a Low-Cost Automated Batch Process", MEMS Symposium, ASME 1999 International Mechanical Engineering Congress and Exposition, November, 1999.
8. A. Cohen, "Electrochemical Fabrication (EFABTM)", Chapter 19 of The MEMS Handbook, edited by Mohamed Gad-El-Hak, CRC Press, 2002.

9. "Microfabrication - Rapid Prototyping's Killer Application", pages 1 - 5 of the Rapid Prototyping Report, CAD/CAM Publishing, Inc., June 1999.

The disclosures of these nine publications are hereby incorporated herein by reference as if set forth in full herein.

The electrochemical deposition process may be carried out in a number of different ways as set forth in the above patent and publications. In one form, this process involves the execution of three separate operations during the formation of each layer of the structure that is to be formed:

1. Selectively depositing at least one material by electrodeposition upon one or more desired regions of a substrate.
2. Then, blanket depositing at least one additional material by electrodeposition so that the additional deposit covers both the regions that were previously selectively deposited onto, and the regions of the substrate that did not receive any previously applied selective depositions.
3. Finally, planarizing the materials deposited during the first and second operations to produce a smoothed surface of a first layer of desired thickness having at least one region containing the at least one material and at least one region containing at least the one additional material.

After formation of the first layer, one or more additional layers may be formed adjacent to the immediately preceding layer and adhered to the smoothed surface of that preceding layer. These additional layers are formed by repeating the first through third operations one or more times wherein the formation of each subsequent layer treats the previously formed layers and the initial substrate as a new and thickening substrate.

Once the formation of all layers has been completed, at least a portion of at least one of the materials deposited is generally removed by an etching process to expose or release the three-dimensional structure that was intended to be formed.

The preferred method of performing the selective electrodeposition involved in the first operation is by conformable contact mask plating. In this type of plating, one or more conformable contact (CC) masks are first formed. The CC masks include a support structure onto which a patterned conformable dielectric material is adhered or formed. The conformable material for each mask is shaped in accordance with a particular cross-section of material to be plated. At least one CC mask is needed for each unique cross-sectional pattern that is to be plated.

The support for a CC mask is typically a plate-like structure formed of a metal that is to be selectively electroplated and from which material to be plated will be dissolved. In this typical approach, the support will act as an anode in an electroplating process. In an alternative approach, the support may instead be a porous or otherwise perforated material through which deposition material will pass during an electroplating operation on its way from a distal anode to a deposition surface. In either approach, it is possible for CC masks to share a common support, i.e. the patterns of conformable dielectric material for plating multiple layers of material may be located in different areas of a single support structure. When a single support structure contains multiple plating patterns, the entire structure is referred to as the CC mask while the individual plating masks may be referred to as "submasks". In the present application such a distinction will be made only when relevant to a specific point being made.

In preparation for performing the selective deposition of the first operation, the conformable portion of the CC mask is placed in registration with and pressed against a selected portion of the substrate (or onto a previously formed layer or onto a previously deposited portion of a layer) on which deposition is to occur. The pressing together of the CC mask and substrate occur in such a way that all openings, in the conformable portions of the CC mask contain plating solution. The conformable material of the CC mask that contacts the substrate acts as a barrier to electrodeposition while the openings in the CC mask that are filled with electroplating solution act as pathways for transferring material from an anode (e.g. the CC mask support) to the non-contacted portions of the substrate (which act as a cathode during the plating operation) when an appropriate potential and/or current are supplied.

An example of a CC mask and CC mask plating are shown in Figures 1(a) - 1(c). Figure 1(a) shows a side view of a CC mask 8 consisting of a conformable or deformable (e.g. elastomeric) insulator 10 patterned on an anode 12. The anode has two functions. Figure 1(a) also depicts a substrate 6 separated from mask 8. One is as a supporting material for the patterned insulator 10 to maintain its integrity and alignment since the pattern may be topologically complex (e.g., involving isolated "islands" of insulator material). The other function is as an anode for the electroplating operation. CC mask plating selectively deposits material 22 onto a substrate 6 by simply pressing the insulator against the substrate then

electrodepositing material through apertures 26a and 26b in the insulator as shown in Figure 1(b). After deposition, the CC mask is separated, preferably non-destructively, from the substrate 6 as shown in Figure 1(c). The CC mask plating process is distinct from a "through-mask" plating process in that in a through-mask plating process the separation of the masking material from the substrate would occur destructively. As with through-mask plating, CC mask plating deposits material selectively and simultaneously over the entire layer. The plated region may consist of one or more isolated plating regions where these isolated plating regions may belong to a single structure that is being formed or may belong to multiple structures that are being formed simultaneously. In CC mask plating as individual masks are not intentionally destroyed in the removal process, they may be usable in multiple plating operations.

Another example of a CC mask and CC mask plating is shown in Figures 1(d) - 1(f). Figure 1(d) shows an anode 12' separated from a mask 8' that comprises a patterned conformable material 10' and a support structure 20. Figure 1(d) also depicts substrate 6 separated from the mask 8'. Figure 1(e) illustrates the mask 8' being brought into contact with the substrate 6. Figure 1(f) illustrates the deposit 22' that results from conducting a current from the anode 12' to the substrate 6. Figure 1(g) illustrates the deposit 22' on substrate 6 after separation from mask 8'. In this example, an appropriate electrolyte is located between the substrate 6 and the anode 12' and a current of ions coming from one or both of the solution and the anode are conducted through the opening in the mask to the substrate where material is deposited. This type of mask may be referred to as an anodeless INSTANT MASK™ (AIM) or as an anodeless conformable contact (ACC) mask.

Unlike through-mask plating, CC mask plating allows CC masks to be formed completely separate from the fabrication of the substrate on which plating is to occur (e.g. separate from a three-dimensional (3D) structure that is being formed). CC masks may be formed in a variety of ways, for example, a photolithographic process may be used. All masks can be generated simultaneously, prior to structure fabrication rather than during it. This separation makes possible a simple, low-cost, automated, self-contained, and internally-clean "desktop factory" that can be installed almost anywhere to fabricate 3D structures, leaving any required clean room processes, such as photolithography to be performed by service bureaus or the like.

An example of the electrochemical fabrication process discussed above is illustrated in Figures 2(a) - 2(f). These figures show that the process involves deposition of a first material 2 which is a sacrificial material and a second material 4 which is a structural material. The CC mask 8, in this example, includes a patterned conformable material (e.g. an elastomeric dielectric material) 10 and a support 12 which is made from deposition material 2. The conformal portion of the CC mask is pressed against substrate 6 with a plating solution 14 located within the openings 16 in the conformable material 10. An electric current, from power supply 18, is then passed through the plating solution 14 via (a) support 12 which doubles as an anode and (b) substrate 6 which doubles as a cathode. Figure 2(a), illustrates that the passing of current causes material 2 within the plating solution and material 2 from the anode 12 to be selectively transferred to and plated on the cathode 6. After electroplating the first deposition material 2 onto the substrate 6 using CC mask 8, the CC mask 8 is removed as shown in Figure 2(b). Figure 2(c) depicts the second deposition material 4 as having been blanket-deposited (i.e. non-selectively deposited) over the previously deposited first deposition material 2 as well as over the other portions of the substrate 6. The blanket deposition occurs by electroplating from an anode (not shown), composed of the second material, through an appropriate plating solution (not shown), and to the cathode/substrate 6. The entire two-material layer is then planarized to achieve precise thickness and flatness as shown in Figure 2(d). After repetition of this process for all layers, the multi-layer structure 20 formed of the second material 4 (i.e. structural material) is embedded in first material 2 (i.e. sacrificial material) as shown in Figure 2(e). The embedded structure is etched to yield the desired device, i.e. structure 20, as shown in Figure 2(f).

Various components of an exemplary manual electrochemical fabrication system 32 are shown in Figures 3(a) - 3(c). The system 32 consists of several subsystems 34, 36, 38, and 40. The substrate holding subsystem 34 is depicted in the upper portions of each of Figures 3(a) to 3(c) and includes several components: (1) a carrier 48, (2) a metal substrate 6 onto which the layers are deposited, and (3) a linear slide 42 capable of moving the substrate 6 up and down relative to the carrier 48 in response to drive force from actuator 44. Subsystem 34 also includes an indicator 46 for measuring differences in vertical position of the substrate which may be used in setting or determining layer thicknesses and/or deposition

thicknesses. The subsystem 34 further includes feet 68 for carrier 48 which can be precisely mounted on subsystem 36.

The CC mask subsystem 36 shown in the lower portion of Figure 3(a) includes several components: (1) a CC mask 8 that is actually made up of a number of CC masks (i.e. submasks) that share a common support/anode 12, (2) precision X-stage 54, (3) precision Y-stage 56, (4) frame 72 on which the feet 68 of subsystem 34 can mount, and (5) a tank 58 for containing the electrolyte 16. Subsystems 34 and 36 also include appropriate electrical connections (not shown) for connecting to an appropriate power source for driving the CC masking process.

The blanket deposition subsystem 38 is shown in the lower portion of Figure 3(b) and includes several components: (1) an anode 62, (2) an electrolyte tank 64 for holding plating solution 66, and (3) frame 74 on which the feet 68 of subsystem 34 may sit. Subsystem 38 also includes appropriate electrical connections (not shown) for connecting the anode to an appropriate power supply for driving the blanket deposition process.

The planarization subsystem 40 is shown in the lower portion of Figure 3(c) and includes a lapping plate 52 and associated motion and control systems (not shown) for planarizing the depositions.

Another method for forming microstructures from electroplated metals (i.e. using electrochemical fabrication techniques) is taught in US Patent No. 5,190,637 to Henry Guckel, entitled "Formation of Microstructures by Multiple Level Deep X-ray Lithography with Sacrificial Metal layers. This patent teaches the formation of metal structure utilizing mask exposures. A first layer of a primary metal is electroplated onto an exposed plating base to fill a void in a photoresist, the photoresist is then removed and a secondary metal is electroplated over the first layer and over the plating base. The exposed surface of the secondary metal is then machined down to a height which exposes the first metal to produce a flat uniform surface extending across the both the primary and secondary metals. Formation of a second layer may then begin by applying a photoresist layer over the first layer and then repeating the process used to produce the first layer. The process is then repeated until the entire structure is formed and the secondary metal is removed by etching. The photoresist is formed over the plating base or previous layer by casting and the voids in the photoresist are formed by exposure of the photoresist through a patterned mask via X-rays or UV radiation.

Electrochemical Fabrication can be used to form structures of complex shape using electrodepositable materials but a need exists for reliable, cost effective, and improved ways of packaging such objects.

Summary of the Invention

5 An object of various aspects of the invention is to provide improved packaging methods for critical structures.

Another object of various aspects of the invention is to provide methods for concurrently fabricating structures and their packaging.

10 Another object of various aspects of the invention is to provide hermetically sealed structures.

Other objects and advantages of various aspects of the invention will be apparent to those of skill in the art upon review of the teachings herein. The various aspects of the invention, set forth explicitly herein or otherwise ascertained from the teachings herein, may address any one of the above objects alone or in combination, or alternatively may not address any of the objects set forth above but instead address some other object ascertained from the teachings herein. It is not intended that all of these objects be addressed by any single aspect of the invention even though that may be the case with regard to some aspects.

20 In a first aspect of the invention an electrochemical fabrication process for producing a three-dimensional structure from a plurality of adhered layers includes: (A) depositing at least a portion of a layer onto the substrate, wherein the substrate may comprise previously deposited material; and (B) forming a plurality of layers such that each successive layer is formed adjacent to and adhered to a previously deposited layer; wherein the layers comprise at least three different materials and
25 wherein the layers contain patterns of material comprising: (1) a desired structural component that is to be protected and that is formed from at least one structural material; (2) a protective enclosure that is formed at least in part from a structural material, wherein at least one portion of the enclosure at least partially surrounds the desired structural component, and wherein the enclosure is limited by at least one
30 opening therein; (3) a sealing material located near the at least one opening; and (4) a sacrificial material located at least partially between the desired structural component to be protected and at least a portion of the enclosure; wherein after formation of the layers at least portion of the sacrificial material located between the

desired structural component and at least a portion of the enclosure is removed; and wherein after the removal of the sacrificial material, the sealing material is made to temporarily flow and seal at least one opening to block or significantly limit a passage of material from an outside of the enclosure to an inside of the enclosure via the at least one sealed opening.

In a second aspect of the invention an electrochemical fabrication process for producing a three-dimensional structure from a plurality of adhered layers, includes: (A) depositing at least a portion of a layer onto a substrate, wherein the substrate may comprise previously deposited material; and (B) forming a plurality of layers such that each successive layer is formed adjacent to and adhered to a previously deposited layer; wherein the layers comprise at least two different materials and wherein the layers contain patterns of material comprising: (1) a desired structural component that is to be protected and that is formed from at least one structural material; (2) a protective enclosure that is formed at least in part from a structural material, wherein at least one portion of the enclosure at least partially surrounds the desired structural component, and wherein the enclosure is limited by at least one opening therein; (3) a sacrificial material located at least partially between the desired structural component to be protected and at least a portion of the enclosure; wherein after formation of the layers at least portion of the sacrificial material located between the desired structural component and at least a portion of the enclosure is removed; and wherein after the removal of the sacrificial material, a seal is formed between the protective enclosure and a sealing structure wherein at least one of the protective enclosure or sealing structure comprises a sealing material that may be used in establishing a sealing of the at least one opening to block or significantly limit a passage of material from an outside of the enclosure to an inside of the enclosure via the at least one sealed opening.

In a third aspect of the invention an electrochemical fabrication process for producing a three-dimensional structure from a plurality of adhered layers includes: (A) depositing at least a portion of a layer onto a substrate, wherein the substrate may comprise previously deposited material; and (B) forming a plurality of layers such that each successive layer is formed adjacent to and adhered to a previously deposited layer; wherein the layers comprise at least two different materials and wherein the layers contain patterns of material comprising: (1) a desired structural component that is to be protected and that is formed from at least one structural

material; (2) a protective enclosure that is formed at least in part from a structural material, wherein at least one portion of the enclosure at least partially surrounds the desired structural component, and wherein the enclosure is limited by at least one opening therein; (3) at least one blocking structure located along a line of sight that
5 includes the at least one opening but spaced from the protective enclosure; and (4) a sacrificial material located at least partially between the desired structural component to be protected and at least a portion of the enclosure; (5) wherein after formation of the layers at least portion of the sacrificial material located between the desired structural component and at least a portion of the enclosure is removed; and (6)
10 wherein after the removal of the sacrificial material, a sealing material is deposited such that it strikes said blocking material which inhibits the sealing material from entering the enclosure in bulk, where by continued build up of the sealing material seals the at least one opening to block or significantly limit a passage of material from an outside of the enclosure to an inside of the enclosure via the at least one
15 sealed opening.

In a fourth aspect of the invention, an electrochemical fabrication process for producing a three-dimensional structure from a plurality of adhered layers includes (A) depositing at least a portion of a layer onto a substrate, wherein the substrate may comprise previously deposited material; and (B) forming a plurality of layers
20 such that each successive layer is formed adjacent to and adhered to a previously deposited layer; wherein the layers comprise at least two different materials and wherein the layers contain patterns of material comprising: (1) a desired structural component that is to be protected and that is formed from at least one structural material; (2) a protective enclosure that is formed at least in part from a structural
25 material, wherein at least one portion of the enclosure at least partially surrounds the desired structural component, and wherein the enclosure is limited by at least one opening therein; and (3) a sacrificial material located at least partially between the desired structural component to be protected and at least a portion of the enclosure.

Further aspects of the invention will be understood by those of skill in the art upon reviewing the teachings herein. Other aspects of the invention may involve
30 combinations of the above noted aspects of the invention and/or addition of various features of one or more embodiments. Other aspects of the invention may involve apparatus that can be used in implementing one or more of the above method aspects of the invention. These other aspects of the invention may provide various

combinations of the aspects presented above as well as provide other configurations, structures, functional relationships, and processes that have not been specifically set forth above.

Brief Description of the Drawings

5 Figures 1(a) - 1(c) schematically depict side views of various stages of a CC mask plating process, while Figures 1(d) - (g) schematically depict a side views of various stages of a CC mask plating process using a different type of CC mask.

 Figures 2(a) - 2(f) schematically depict side views of various stages of an electrochemical fabrication process as applied to the formation of a particular
10 structure where a sacrificial material is selectively deposited while a structural material is blanket deposited.

 Figures 3(a) - 3(c) schematically depict side views of various example subassemblies that may be used in manually implementing the electrochemical fabrication method depicted in Figures 2(a) - 2(f).

15 Figures 4(a) - 4(i) schematically depict the formation of a first layer of a structure using adhered mask plating where the blanket deposition of a second material overlays both the openings between deposition locations of a first material and the first material itself.

20 Figure 5(a) depicts a block diagram of the basic steps of a first group of embodiments.

 Figure 5(b) presents the basic steps of a second group of embodiments in the form of a block diagram.

 Figures 6(a) - 6(c) depict a side view of various stages in the production of a structure according to a preferred embodiment of the invention.

25 Figure 6(d) depicts a top view of the upper two layers of the structure of Figure 6(b) separated and then overlaid.

 Figure 7(a) and 7(b) depict to alternative configurations of the sealing layer of Figure 6(b)

30 Figure 8(a) depicts a side view of an alternative configuration for the final two layers of Figure 6(b) while 8(b) depicts a top view of the upper two layers of the alternative structure first separated one from the other and then overlaid.

 Figures 9(a) - 9(d) depict side views and top views illustrating features of an alternative opening and sealing configuration for an enclosing wall.

Figures 10(a) - 10(h) depict various alternative opening and sealing configurations.

Figures 11(a) - 11(c) depict various alternative opening and sealing configurations.

5 Figures 12(a) - 12(c) depict various alternative opening and sealing configurations.

Figures 13(a) and 13(b) depict an alternative opening and sealing technique

Figures 14(a) and 14(b) depict an alternative technique for sealing openings.

10 Figures 15(a) - 15(f) depict side views of various states of an alternative embodiment for packaging a structure.

Figures 16(a) - 16(f) depict side views of various states of another embodiment for packaging a structure.

Figure 17(a) and 17(b) depict side views associated with an alternative configuration for removing sacrificial material and for sealing a package.

15 Figures 18(a) - 18(b) depict side views for an alternative configuration for removing sacrificial material and for sealing a package.

Figure 18(c) depicts a side top view corresponding the enclosure and lid of Figure 18(a)

20 Figure 18(d) depicts a side view for an alternative configuration for removing sacrificial material and for sealing a package.

Detailed Description

Figures 1(a) - 1(g), 2(a) - 2(f), and 3(a) - 3(c) illustrate various features of one form of electrochemical fabrication that are known. Other electrochemical fabrication techniques are set forth in the '630 patent referenced above, in the various
25 previously incorporated publications, in various other patents and patent applications incorporated herein by reference, still others may be derived from combinations of various approaches described in these publications, patents, and applications, or are otherwise known or ascertainable by those of skill in the art from the teachings set forth herein. All of these techniques may be combined with those of the various
30 embodiments of various aspects of the invention to yield enhanced embodiments. Still other embodiments may be derived from combinations of the various embodiments explicitly set forth herein.

Figures 4(a)-4(i) illustrate various stages in the formation of a single layer of a multi-layer fabrication process where a second metal is deposited on a first metal as well as in openings in the first metal where its deposition forms part of the layer. In Figure 4(a), a side view of a substrate 82 is shown, onto which patternable photoresist 84 is cast as shown in Figure 4(b). In Figure 4(c), a pattern of resist is shown that results from the curing, exposing, and developing of the resist. The patterning of the photoresist 84 results in openings or apertures 92(a) - 92(c) extending from a surface 86 of the photoresist through the thickness of the photoresist to surface 88 of the substrate 82. In Figure 4(d), a metal 94 (e.g. nickel) is shown as having been electroplated into the openings 92(a) - 92(c). In Figure 4(e), the photoresist has been removed (i.e. chemically stripped) from the substrate to expose regions of the substrate 82 which are not covered with the first metal 94. In Figure 4(f), a second metal 96 (e.g., silver) is shown as having been blanket electroplated over the entire exposed portions of the substrate 82 (which is conductive) and over the first metal 94 (which is also conductive). Figure 4(g) depicts the completed first layer of the structure which has resulted from the planarization of the first and second metals down to a height that exposes the first metal and sets a thickness for the first layer. In Figure 4(h) the result of repeating the process steps shown in Figures 4(b) - 4 (g) several times to form a multi-layer structure are shown where each layer consists of two materials. For most applications, one of these materials is removed as shown in Figure 4(i) to yield a desired 3-D structure 98 (e.g. component or device).

The various embodiments, alternatives, and techniques disclosed herein may be used in combination with electrochemical fabrication techniques that use different types of patterning masks and masking techniques. For example, conformable contact masks and masking operations may be used, proximity masks and masking operations (i.e. operations that use masks that at least partially selectively shield a substrate by their proximity to the substrate even if contact is not made) may be used, non-conformable masks and masking operations (i.e. masks and operations based on masks whose contact surfaces are not significantly conformable) may be used, and adhered masks and masking operations (masks and operations that use masks that are adhered to a substrate onto which selective deposition or etching is to occur as opposed to only being contacted to it) may be used.

Figure 5(a) presents the basic steps of a first group of embodiments of the invention in the form of a block diagram. Block 102 calls for the formation of a group of electrochemically fabricated layers that include: (1) structural component(s) that are to be protected; (2) a protective enclosure formed from a structural material but having at least one opening therein; (3) a sealing material located near the at least one opening; and (4) a sacrificial material located at least partially between the structure to be protected and the protecting enclosure. The electrochemical fabrication process used may be similar to the one illustrated in Figures 1(a) - 1(c) and 2(a) - 2(f) or it may be another process set forth in the '630 patent, a process set forth in one of the other previously incorporated publications, a process described in one of the patents or applications that is included in the listing of incorporated patents and applications set forth hereafter, or the process may be a combination of various approaches described in these publications, patents, and applications, or otherwise known or ascertainable by those of skill in the art.

After the layers are formed the process proceeds to block 104 which calls for the removal of the sacrificial material.

Next, at block 106, the process calls for the optional evacuation of the region(s) between the enclosure and the structure to be protected. The process may also include the back filling of the regions with a desired fill gas. The fill gas, for example, may be inert (e.g. N₂, Ar, or the like) or it may be chemically active such as providing a reducing environment (e.g. H₂). The process may also include some special processing that is useful for preparing the structure/enclosure combination for the next operation.

Finally, at block 108, the sealing material is temporarily made to flow and to close the at least one opening.

Figures 6(a) - 6(c) present side views of various stages of the process flow of Figure 5(a) as applied to a specific structure. Figure 6(a) depicts the group of layers 112 electrochemically fabricated and attached to a substrate 114. The group of layers includes (1) a structural component 122 that is to be protected and formed from a structural material; (2) a protective enclosure 124 formed from a structural material but having multiple openings 126 therein; (3) a sealing material 128 located near the openings; and (4) a sacrificial material 132 that fills the interior 134 (i.e. cavity) of the enclosure 124.

Figure 6(b) depicts the substrate 114, the enclosure 124, the structural component 122, and the sealing material 128 after removal of the sacrificial material but before flowing, sealing, and resolidification of the sealing material. The sacrificial material is preferably removed by etching with the etchant entering the cavity
5 through the opening in the enclosure.

Figure 6(c) depicts the substrate 114, the enclosure 124, the structural component 122, and the sealing material 128 after flowing, sealing, and resolidification of the sealing material. In this embodiment, the structural component becomes protected within the package defined by the enclosure and the substrate.
10 In the present embodiment the sealing material is preferably a low melting temperature electroplatable metal or solder-like material such as Indium (In) or Tin (Sn)/Lead (Pb). The sacrificial material may be copper and the structural material may be nickel, though of course other appropriate materials would be acceptable. The requirement being that the etching of the sacrificial material should not damage
15 the structural component 122 or significant damage the sealing material 128.

Figure 6(d) depicts a top view of the upper most layers of Figure 6(b). The left most component 142 is the second to last layer which is the lid of enclosure 124 and which is made from the structural material and which includes openings 126. Component 144 is the last layer of the structure and is made from a sealing material
20 128. It also includes openings 126. Component 144 is surrounded by a dashed boundary line 148 which illustrates the outer boundary of component 142 when the two components are aligned. Component 146 shows a top view of the two components 142 and 144 overlaid with the openings 124 aligned.

Figure 7(a) and 7(b) depict to alternative configurations of the sealing layer of Figure 6(b). In Figure 7(a) the sealing material include a single cross-bar 152 that bridges the openings as it is believed that such a bridge might aid in closing the opening when the sealing material is made to flow (e.g. by heating sufficiently). Figure 7(b) is similar to Figure 7(a) with the exception that two crossed bridging elements 154 and 156 are depicted.

Figure 8(a) depicts a side view of an alternative configuration for the final two layers of Figure 6(b) while 8(b) depicts a top view of the last two layers including the alternative sealing layer. The second to last layer 142 has not changed its configuration from that which was depicted in Figure 6(d) whereas the final layer 144' has been modified. Instead of the last layer being configured as a rectangular plate

with holes in it as was the case in Figures 6(a) - 6(d), in Figures 8(a) and 8(b) the sealing material around each opening is in the form a ring as can be best seen in Figure 8(b) and more particularly the rings have smaller inner diameter than do the holes 126 in layer 142. It is believed that the partial overlap of the sealing material with the holes 126 in layer 142 will aid in causing the material to fill in and seal the openings when the sealing material is made to flow.

Figure 9(a) depicts a side view of an enclosure that is formed from a structural material with the exception of the third to last layer from the top which is a sealing material layer 162. The sealing material layer is shown from a top view in Figure 9(b) where a plurality of openings 126' through the sealing layer can be seen. Upon flowing of the sealing material it is believed that the material will spread and collapse to bridge the openings and seal them. The collapse of the sealing layer can be seen in the side view of Figure 9(c). The spreading of the sealing material and the closing of the openings can be seen in the top view of Figure 9(d) wherein the dashed structures represent the original configuration of sealing material layer 162 and the spread out material 166 the new configuration after flowing. In alternative embodiments, the collapse of the sealing layer and the spread of sealing material may be aided by application of a pressure or force to the upper portion of the structure.

Figures 10(a) depicts a thickness (e.g. 1 or more layers) of an enclosure 172 made from a structural material and having an opening 174 therein with sloped faces 176. A sealing material layer 178 is shown above the layer of structural material. The sloped faces 176 are shown with stair steps though in some embodiments they may be more truly of a sloped configuration. It is believed that the sloping (or small stair steps) may help the flowable sealing material wet the surface of the opening 174 when the sealing material is made to flow and thus will aid in the closure of the opening. Figure 10(b) shows the resulting closure of the opening of Figure 10(a) after the sealing material is made to flow and allowed to resolidify.

Figure 10(c) shows the a top view of an opening of Figure 10(a) when the opening is circular in nature and the stair steps are circles of progressively varying inner diameter. Figure 10(d) depicts another alternative to the openings of Figure 10(a) where the openings are indicated to be substantially circular but with radial openings cut through which increase the size of the opening for improved entry of etchant and removal of sacrificial material but still not forming such a large opening

that the sealing material would have a difficult time bridging the gaps. Figure 10(e) is analogous to Figures 10(c) and 10(d) but for rectangular holes as opposed to circular holes. Though the openings in Figure 10(e) are shown almost as square in shape, in actual practice they may be elongated with slopes on each side of the elongated
5 openings. If elongated the slots through the stair steps may be increased in number.

Figure 10(f) shows an alternative configuration for the sealing material 178 in relation to an opening 174 in the enclosure structure 172. The sealing materials extend symmetrically beyond the edges of each side of the upper portion of the opening in enclosure 172. It is believed that such a configuration will aid in the
10 closure of the hole once the material is made to flow. Figure 10(g) depicts an alternative configuration to that of Figure 10(f) in that a portion of the overhanging sealing material is made to extend substantially beyond the midpoint of opening and preferably substantially over the lower portion of the structure bounding the opposite
15 side of the opening such that when the flowable material is heated it may flow and collapse on the far side of the opening and thereby sealing it. Figure 10(h) is a further alternative to the configuration of 10(f) in that the structural material is formed in such away that that the opening through the structural material is non-symmetric and as with Figure 10(g) is not centered with the opening in the sealing material 178.
20 Figure 10(i) depicts a further alternative where the overhanging portion includes a bulge 180 of sealing material attached thereto. It is believed that this bulge of material will be useful in aiding the closure of the opening once the sealing material is made to flow. In other alternatives, the bulge of material may be extended to largely cover the entire right side of the sloped surface

25 Figure 11(a) depicts five layers of structural material 181 - 185 forming a portion of an enclosure and having an opening 186 therein. The structural layers are configured to have a protrusion 188 jutting into the opening. Above the protrusion is a quantity of sealing material 192. Once the sealing material is made flowable it is believed that the protrusion 188 will help force the sealing material to bridge the gap
30 in this narrowed region and will help hold the sealing material in place once contact between the sides is made. In this embodiment as well as in others, it may be particularly useful to treat the enclosure with a reducing gas or other activation process after removing the sacrificial material but before the sealing material is made to flow. The activation of the surface may help in causing the flowable sealing

material to wet the surface of the structural material. In particular, if the structural material is subjected to activation, and the activation is initiated from one side of the opening, it may be desirable to have the sealing material toward the opposite side of the opening as it may be anticipated that side nearest the initiation will be more highly activated and thus the flowing material will have a tendency to move in that direction as it wets the surface of the structural material. As such, if the sealing material is toward the inside of the enclosure, and activation is initiated from outside the enclosure, the higher level of activation may be toward the outer extends of the opening and the flowing of the material will be encourage to move in the right direction for sealing the opening.

Figure 11(b) depicts an alternative configuration for the sealing material. This alternative configuration may keep the sealing material from having to flow across any unwetted structural material surfaces in that the sealing material is deposited over the protrusions and thus need only internally bulge due to surface tension forces. In embodiments of this type, it may not be necessary or desirable to activate the surfaces of the structural material. Figure 11(c) depicts another alternative where a bulge of sealing material is provided within a pocket 194 adjacent to the opening. It is believed that such a pocket of material adjacent to thinner regions 196 of sealing material might tend to draw material from those thinner regions as surface tension drives the sealing material to minimize its surface area thus increasing the bulging of the pocket to help seal the opening.

Figures 12(a) - 12(c) depict before and after versions of deposited and flowed sealing material for different potential opening configurations. In these configurations the structural material is given reference numeral 202 and the deposited sealing material is given reference numeral 204 and the flowed sealing material is given reference numeral 204'.

Figure 5(b) presents the basic steps of a second group of embodiments of the invention in the form of a block diagram. In this Figure like elements to those in Figure 5(a) are given like reference numerals. Block 102', calls for the formation of a group of electrochemically fabricated layers that include: (1) structural component(s) that are to be protected; (2) a protective enclosure formed from a structural material but having at least one opening therein; and (3) a sacrificial material located at least partially between the structure to be protected and the protecting enclosure. Block

102' also indicates that the formed layers may also include a sealing material located near the at least one opening.

After the layers are formed the process proceeds to block 104 which calls for the removal of the sacrificial material. This may be performed in any manner that
5 allows selective removal of the sacrificial material without damaging the structural material (e.g. by selective chemical etching or melting).

Next, at block 106, the process calls for the optional evacuation of the region(s) between the enclosure and the structure to be protected. The process may also include the back filling of the regions with a desired fill gas. The fill gas, for
10 example, may be inert (e.g. N₂, Ar, or the like) or it may be chemically active such as providing a reducing environment (e.g. H₂) The process may also include some special processing that is useful for preparing the structure/enclosure combination for the next operation.

Next, the process moves forward to block 110 which calls for moving a
15 sealing structure into position relative to the rest of the enclosure. The sealing structure may include a sealing material. Typically at least one of the layers formed or the structure will include a sealing material. One of the enclosure or the sealing structure may also or alternatively include an adhesive. The movement of the sealing structure may be by translation, rotation, or some combination thereof. The
20 movement may occur, for example, by pushing with a structure, by air pressure, by collapse as the sacrificial material is removed, by movement induced by stresses built in during layer-by-layer formation, by causing a phase change or the like to occur that causes a relative motion to result, or the like.

Finally, at block 108', the sealing material is temporarily made to flow while
25 the enclosure and sealing structure are brought or held together.

Figures 13(a) and 13(b) depict an example according to one of the embodiments of the group outlined in Figure 5(b). Figure 13(a) depicts a lid 212 located above the walls 214. The walls are topped with sealing material 216. After removal of any sacrificial material (not shown) the lid is brought down into position
30 and the sealing material 216 is made to flow (e.g. by the lid being heated). The sealing material is compressed and forms seals between the lid and the walls. The lid 212 may be made by an electrochemical fabrication process or be made in some other manner. The lid may be of a different material than the rest of the enclosure. The lid may be a dielectric or even a transparent material.

In some embodiments, like that shown in Figures 13(a) and 13(b) the walls of the enclosure are co-fabricated with the structure but the lid is not. The walls may or may not have etching holes in them. The last layer of the structure formed may have a sealant applied (e.g. some type of solder) which may or may not be planarized.

- 5 After etching to release the structure in the box, the separately fabricated lid (e.g. a metal sheet of some kind) is placed over the build. This may be done at the wafer scale or on individual devices. The solder (or other material) is made to flow and the device is sealed. This approach offers several advantages: (1) the devices or structures can be easily, visually examined prior to sealing; (2) additional processing
- 10 (e.g., metallization, passivation, testing, etc.) may be performed prior to sealing; (3) release etching will be less problematic; (4) problems with the application or planarization of the flowable material may be minimized; (5) it may be cheaper since one or more EFAB produced layers can be eliminated by use of an essentially unpatterned sheet, (6) the lid may be made of a material that is not easily
- 15 electrodeposited; and (7) wetting of the wall surfaces and lid surface by the solder become less critical as a result of being able to press the lid and the wall surfaces together.

In some alternative embodiments, the solder (or other flowable sealing material) may be deposited onto the lid as opposed to on the walls.

- 20 Many alternatives to the above noted embodiments are possible and many additional embodiments will be apparent to those of skill in the art. Multiple structural materials may be used. Multiple types of flowable materials may be used. Structural component(s) and enclosures may be formed from different materials or even multiple materials. One or more of the flowable materials may be used for sealing
- 25 while others may be used for causing displacement of structures relative to one another and thus may aid in the automatic sealing of structures after removal of any sacrificial materials. Interconnects may be fed through the enclosures or the substrate so that electric connection to the structure inside the enclosure can be established. Lid structures or substrates may have openings covered by transparent
- 30 windows such that optical components may be embedded inside the enclosures and optical signals transmitted into and out of the enclosures. The substrate may include a conductively coated transparent structure (e.g. glass) where the coating may be removed in conjunction with the removal of the sacrificial material or be removed subsequent to the removal of the sacrificial material. Alternatively, a sufficiently

conductive and optically transmissive coating may be applied to a transparent substrate such as glass, quartz, and the like.

Various techniques may be used to improve and supplement the processes described above.

5 IR reflow may be used to make heating more uniform and to minimize the heating of the structures to be protected (e.g. devices) and the substrate. In this process an IR source larger than the substrate is placed parallel to the solder layer and at a fixed distance. The substrate can be relatively translated in perpendicular to the plane of the layers (i.e. along the z-axis) to bring it into proximity with the IR
10 source or it can be moved on a conveyor past the source or it can be fixed in place before heat is applied.

An alternative heating approach involves the use of a hot plate. In this approach, the solder layer or lid of structural material contacting the solder is brought into actual contact with a hot plate. The plate could be treated to improve the wetting
15 of the solder. The plate may be brought into contact by translation along the z-axis, and may be removed by lateral translation. In a more extreme case, the plate could carry the solder and the packaging layer would not have to be plated with solder. In an alternative to the use of the hot plate it may be possible to bring the layer with openings into contact with molten sealing material (e.g. solder that has been made
20 molten) which will wet and cling to the surface when it is moved away and will seal the opening(s).

Various surface treatments may be used to improve the wetting of the sealing material (e.g. solder) to the structural material. Chemical treatments may be used such as fluxes, resins, surface activators. It is also possible for Electro-chemical and
25 plasma treatments to be used. It may be possible to add surface treatment chemicals to the etchant that is used to remove the sacrificial material.

Reduction processes may be used to reduce oxide layers that can impede the flow of the sealing material and thus improve wetting. As an implementation example, before sealing material is made to flow, a reducing atmosphere (e.g.,
30 hydrogen) is provided. The sealing material is held below its melting point until oxide layers are fully reduced. The reducing atmosphere may then be replaced with an inert gas (e.g. N₂). The inert gas may then be evacuated to create an evacuated space or it may be retained. While the enclosure remains evacuated or filled with a desired gas, the temperature may be increased to the reflow temperature or to

desired temperature above the reflow temperature such that flowing of the sealing material results in sealing after which the temperature may be reduced to allow solidification of the molten sealing material.

5 In some embodiments wicking structures may be used to aid in the flow of sealing material. Ideally, openings should be sized and located to give the maximum area for etchant flow, but provide the minimum challenge for wetting with sealing material. Circular openings may not be optimal and long narrow openings (slots) or star shapes may be better, but still other alternatives may exist. Circular opening can be made more likely to occlude (i.e. seal) by adding wetting structures. A simple
10 wetting structure is a line that bisects the opening as was illustrate in Figure 7(a). The line may be in either of the structural material or the sealing material or in both (e.g. adjacent to one another). The line may arch out of the planes of the layers or otherwise be of a non-linear shape (e.g. curved or of varying dimension). A more complex wetting structure may have one or more concentric rings connected by one
15 or more sets of lines (e.g. two sets of bisecting lines).

In still other embodiments, it may be possible to perform a deposition to fill the holes, particularly if such a deposition is essentially a straight line deposition process and if underneath the holes a structural element is located that can act as a deposition stop and build up point from which the deposit can build up to seal the
20 openings. This is illustrated with the aid of Figures 14(a) and 14(b). Figure 14(a) depicts a wall or lid of a packaging structure 302 below which a component to be sealed exists (not shown). The wall or lid contains openings 304 below which blocking elements 306 exist. Any sacrificial material located below the wall or lid 302 is removed, at least in part, via openings 304. After removal, the package may be
25 filled with a desired gas or other material or it may remain evacuated. A substantially or at least largely straight line deposition process (e.g. via PVD) may be used to deposit sufficient material into the holes such the holes become sealed. Such sealing is illustrated in Figure 14(b) via the deposition of material 308. In Figure 14(b) the deposition of material 308 is indicated as being selectively applied. In
30 other alternatives, the material may be deposited in a blanket fashion.

In other embodiments, to enhance the hermetic sealing of a solder-type sealer, it may be possible to perform a PVD or other deposition operation over the sealed openings to deposit a material tends to be more hermetic in its properties (e.g. metal or glass). In still other embodiments it may be possible to perform an

electrodeposition operation over the solder sealed openings to enhance the sealing. In other embodiments, a sealed package may include a getter material.

Another embodiment is explained the aid of Figures 15(a) - 15(f). In Figure 15(a), a device 424 (e.g., a capacitor as shown here) has been fabricated, top layer
5 first, on a metallic release layer 408 (e.g., low-melting point solder) applied to a temporary substrate 402. In Figure 15(b), prior to attachment of the final substrate, the sacrificial material 420 has been partly etched. As much etching is done as is possible at this time, though preferably not so much as to completely release the device inside the package, since the device as a whole and its individual
10 components may then shift from their intended positions. To allow for prolonged etching, each independent element of the device may be provided with an anchoring segment (not shown or required in this example) which extends upwards so that it is embedded within the sacrificial material during this initial etch, if the element otherwise (e.g., due to its relatively short height) would become unanchored. In
15 embodiments where structures are otherwise joined to the side walls complete etching may be acceptable.

In Figure 15(c), the structure has been adhered to a final substrate 432 that is coated with an adhesive layer 438 (unless the substrate is made from a thermoplastic or other material which can itself adhere to the structural material). The
20 adhesive is preferably of a type that allows for a hermetic or near-hermetic seal to be achieved, and preferably has good adhesion to the structural material.

In Figure 15(d), the release layer is shown as having been removed (e.g., by melting if a solder) and the temporary substrate has been removed (if necessary, any residue of the release layer can be removed by etching, lapping, polishing, etc.).
25 In Figure 15(e), the remaining sacrificial material has been etched through the holes in the package. In Figure 15(f), the solder (typically with a higher melting point than the solder used for the release layer) is melted to seal the device (this step is normally performed within a heated chamber filled with the desired gas or within a vacuum chamber).

30 Another embodiment is illustrated in Figure 16(a) - 16(f). In this embodiment, individual isolated elements of the structure (component, device, etc.) are anchored to other elements and the inside surfaces of the package so as to allow complete etching of the sacrificial material while isolated element retain their positions. Only a single small hole 446 is required to be sealed by solder 450 (in some alternatives

multiple holes may be supplied), and this hole, along with the adjacent solder, is not required if the interior of the package can be air at atmospheric pressure (vs. an inert gas or a vacuum, for example), or if the operation of attaching the structure 424 and enclosure 462 to the final substrate 480 can be accomplished while in an environment of a desired gas or a vacuum. The only remaining purpose for the hole and solder is to allow the internal atmosphere of the package to be created after 'substrate swapping' is completed. In Figure 16(a), a device 424 has been fabricated, top layer first, on a metallic release layer 474 (e.g., low-melting point solder) applied to a temporary substrate 444. High-aspect ratio 'pillars' 456 of high-melting point solder (in fact, a low-melting point solder can also be used, in which case the pillars will detach during step leading to the state depicted in Figure 16(d), vs. during a separation operation depicted as being completed in Figure 16(e)) have been provided to anchor the individual elements of the device during the subsequent etch. In Figure 16(b), prior to attachment of the final substrate 480, the sacrificial material 468 has been completely etched. In Figure 16(c), the structure has been adhered to a final substrate that is coated with an adhesive layer 486. In Figure 16(d), the release layer 474 is shown as being removed or otherwise being made to release its grip on temporary substrate 444 and the temporary substrate is shown as being removed. In Figure 16(e), the higher-melting point solder 456 is melted to seal the device and to cause the pillars to 'ball up' since they become unstable when melted due to their high aspect ratio (length/diameter).

Another group of embodiments provide enclosure with moveable attached sealing structures (e.g. lids). In these embodiments the sealing structure is initially located to allow etching and is then moved or dropped into sealing position. The attachment of the sealing structure to the enclosure allows the lid to remain attached to the enclosure during etching and possibly to thereafter be positioned with enhanced alignment. In some embodiments, the attachment elements may be supplemented by one or more alignment elements. In some of these embodiments one or more attachment elements and/or alignment elements may be used. In some embodiments, these attachment and/or alignment elements may be located on the perimeter of the enclosure and/or sealing structure. In some alternative embodiments, they may be located to the interior of the perimeter of the enclosure or sealing structure.

In some embodiments, movement of the sealing structure relative to the enclosure may cause alignment or attachment elements to progress further into the interior of the enclosure thereby necessitating existence of sufficient clearance between the elements and the structure (device) to be packaged. In some alternatives the alignment and/or attachment elements may be mounted on the enclosure itself and thereby not cause a shrinking of the interior space of the enclosure as sealing occurs.

An example of a structure configured and packaged according to this group of embodiments is depicted in Figures 17(a) and 17(b) which schematically depict side views of a package and structure in a pre-sealed state and a sealed state. Figure 17(a) depicts a sealing structure or lid element 508 having an attachment element 510. The lid element 508 is spaced from an enclosure 506 which is mounted to a substrate 502 which together define an interior region 514 in which a structure 504 is located. The attachment element 510 protrudes through an opening in a retainment structure which forms part of enclosure 506. Lid 508 and/or enclosure 506 (both as depicted) include a sealing material 512 (e.g. solder or a sealable adhesive). Figure 17(b) depicts the enclosure and lid after they have been mated. The sealing material may then be melted or otherwise made to seal the enclosure.

In the depicted example, the flow passages for etching the structure are located along the perimeter of the enclosure. This may be acceptable in some embodiments, but if the enclosure is relatively wide excess of etchant only from the edges or perimeter of the structure may cause problems (e.g. slow etching time, damage to the perimeter of the structure as a result of exposure to etchant, and the like). In other embodiments other passage and sealing configurations are possible (e.g. in which passages are supplied throughout the interior portions of the lid).

The structure and enclosure or preferable upside down during etching of the sacrificial material (e.g. copper) or are otherwise subjected to different orientations. When all the sacrificial material is etched, the lid is free to move and the structure and enclosure are dried and may be laid right side up so the lid "falls" into a seated position on top of a thin plated solder layer as shown in Figure 17(b). Next the package is heated to form a solder weld between lid and enclosure to complete the packaging. As depicted both the lid and the enclosure could have perimeters of solder plating so wetting of structural material is not necessary.

Figures 18(a) - 18(d) depict other alternative configurations that may have utility in sealing enclosures. As noted above etching holes located within the interior of a lid or enclosure can be useful in decreasing time to etch and in some configurations such holes need not be tied to a size that can be sealed by a filling solder. Figure 18(a) depicts an enclosure 522 having sealing material 524 located near openings that extend through holes 526. Moveably attached to the enclosure is lid element 528 that is formed in lower position and can be moved higher once etching has been completed and it is desired to seal the structure. The lid element includes openings 536 that extend through it and are offset slightly from the openings 526. Figure 18(b) depicts the enclosure and lid when relatively positioned to yield a closed state at which point sealing can occur. Figure 18(c) shows a top view of the structure of Figure 18(a) wherein lid element 528 can be seen through the holes 506 that extend through enclosure 522. The holes 516 in lid 528 are shown with dashed lines.

Figure 18(d) shows an alternative configuration where the attachment structures are located on the perimeter of the enclosure 538 and where enclosure portions 540 (forming a groove with a lip to catch the lid 546), may include openings 544 that can aid in providing excess to etchant.

In some alternative embodiments the packaging techniques disclosed herein may be implemented without necessarily hermetically sealing the structure within the enclosure.

In some alternative embodiments solder may be deposited or formed in ways that minimum or even eliminate the need for it to be planarized (e.g. possibly by selective deposition to heights lower than the next planarization level or deposition in voids, etc.

In other alternative embodiments, the lids need not be planar or feature less, the lids (i.e. the other half of the enclosure may contain structural components that have been electrochemically fabricated or that have been produced in some other manner.

In other alternative embodiments, a lid may be placed over an enclosure after etching away the sacrificial material and the lid may be covered (particularly in the bridging region from the lid to the enclosure) with an epoxy or other material to complete the sealing operation. In other embodiments, the lid may be matted to the enclosure via a tapered surface. In still other embodiments the solder, other

mettable materials, adhesive, and the like may be used in establishing a preliminary bond or seal between the enclosure and the lid while an over coating with an epoxy, or other material (e.g. electrodeposited, sputtered, or other applied metal) may be used to enhance the integrity of the packaging.

5 The patent applications and patents set forth below are hereby incorporated by reference herein as if set forth in full. The gist of each patent application or patent is included in the table to aid the reader in finding specific types of teachings. It is not intended that the incorporation of subject matter be limited to those topics specifically indicated, but instead the incorporation is to include all subject matter
10 found in these applications. The teachings in these incorporated applications can be combined with the teachings of the instant application in many ways: For example, enhanced methods of producing structures may be derived from the combination of teachings, enhanced structures may be obtainable, enhanced apparatus may be derived, and the like.

15 U.S. Patent Application No. 09/488,142, filed January 20, 2000, and entitled "An Apparatus for Electrochemical Fabrication Comprising a Conformable Mask" is a divisional of the application that led to the above noted '630 patent. This application describes the basics of conformable contact mask plating and electrochemical fabrication including various alternative methods and apparatus for practicing EFAB
20 as well as various methods and apparatus for constructing conformable contact masks.

 U.S. Patent Application No. 60/415,374, filed on October 1, and 2002, and entitled "Monolithic Structures Including Alignment and/or Retention Fixtures for
Accepting Components" is generally directed to a permanent or temporary alignment
25 and/or retention structures for receiving multiple components are provided. The structures are preferably formed monolithically via a plurality of deposition operations (e.g. electrodeposition operations). The structures typically include two or more positioning fixtures that control or aid in the positioning of components relative to one another, such features may include (1) positioning guides or stops that fix or at least
30 partially limit the positioning of components in one or more orientations or directions, (2) retention elements that hold positioned components in desired orientations or locations, and (3) positioning and/or retention elements that receive and hold adjustment modules into which components can be fixed and which in turn can be used for fine adjustments of position and/or orientation of the components.

U.S. Patent Application No. XX/XXX,XXX, (Corresponding to MEMGen Docket No. P-US026-A-MG), filed on April 21, 2003, and entitled "Methods of Reducing Discontinuities Between Layers of Electrochemically Fabricated Structures" is generally directed to various embodiments providing electrochemical fabrication methods and apparatus for the production of three-dimensional structures from a plurality of adhered layers of material including operations or structures for reducing discontinuities in the transitions between adjacent layers. Some embodiments improve the conformance between a size of produced structures (especially in the transition regions associated with layers having offset edges) and the intended size of the structure as derived from original data representing the three-dimensional structures. Some embodiments make use of selective and/or blanket chemical and/or electrochemical deposition processes, selective and or blanket chemical and/or electrochemical etching process, or combinations thereof. Some embodiments make use of multi-step deposition or etching operations during the formation of single layers.

U.S. Patent Application No. XX/XXX,XXX, (Corresponding to MEMGen Docket No. P-US029-A-MG), filed on May 7, 2003, and entitled "EFAB With Selective Transfer Via Instant Mask" is generally directed to three-dimensional structures that are electrochemically fabricated by depositing a first material onto previously deposited material through voids in a patterned mask where the patterned mask is at least temporarily adhered to a substrate or previously formed layer of material and is formed and patterned onto the substrate via a transfer tool patterned to enable transfer of a desired pattern of precursor masking material. In some embodiments the precursor material is transformed into masking material after transfer to the substrate while in other embodiments the precursor is transformed during or before transfer. In some embodiments layers are formed one on top of another to build up multi-layer structures. In some embodiments the mask material acts as a build material while in other embodiments the mask material is replaced each layer by a different material which may, for example, be conductive or dielectric.

U.S. Patent Application No. XX/XXX,XXX, (Corresponding to MEMGen Docket No. P-US030-A-MG), filed on May 7, 2003, and entitled "Three-Dimensional Object Formation Via Selective Inkjet Printing & Electrodeposition" is generally directed to three-dimensional structures that are electrochemically fabricated by

depositing a first material onto previously deposited material through voids in a patterned mask where the patterned mask is at least temporarily adhered to previously deposited material and is formed and patterned directly from material selectively dispensed from a computer controlled dispensing device (e.g. an ink jet nozzle or array or an extrusion device). In some embodiments layers are formed one on top of another to build up multi-layer structures. In some embodiments the mask material acts as a build material while in other embodiments the mask material is replaced each layer by a different material which may, for example, be conductive or dielectric.

U.S. Patent Application No. 10/271,574, filed on October 15, 2002, and entitled "Methods of and Apparatus for Making High Aspect Ratio Microelectromechanical Structures" is generally directed to various embodiments of the invention presenting techniques for forming structures (e.g. HARMS-type structures) via an electrochemical extrusion (ELEX™) process. Preferred embodiments perform the extrusion processes via depositions through anodeless conformable contact masks that are initially pressed against substrates that are then progressively pulled away or separated as the depositions thicken. A pattern of deposition may vary over the course of deposition by including more complex relative motion between the mask and the substrate elements. Such complex motion may include rotational components or translational motions having components that are not parallel to an axis of separation. More complex structures may be formed by combining the ELEX™ process with the selective deposition, blanket deposition, planarization, etching, and multi-layer operations of EFAB™.

U.S. Patent Application No. 60/435,324, filed on December 20, 2002, and entitled "EFAB Methods and Apparatus Including Spray Metal or Powder Coating Processes", is generally directed to various embodiments of the invention presenting techniques for forming structures via a combined electrochemical fabrication process and a thermal spraying process. In a first set of embodiments, selective deposition occurs via conformable contact masking processes and thermal spraying is used in blanket deposition processes to fill in voids left by selective deposition processes. In a second set of embodiments, selective deposition via a conformable contact masking is used to lay down a first material in a pattern that is similar to a net pattern that is to be occupied by a sprayed metal. In these other embodiments a second material is blanket deposited to fill in the voids left in the first pattern, the two

depositions are planarized to a common level that may be somewhat greater than a desired layer thickness, the first material is removed (e.g. by etching), and a third material is sprayed into the voids left by the etching operation. The resulting depositions in both the first and second sets of embodiments are planarized to a desired layer thickness in preparation for adding additional layers to form three-dimensional structures from a plurality of adhered layers. In other embodiments, additional materials may be used and different processes may be used.

U.S. Patent Application No. 60/429,483, filed on November 26, 2002, and entitled "Multi-cell Masks and Methods and Apparatus for Using Such Masks to Form Three-Dimensional Structures" is generally directed to multilayer structures that are electrochemically fabricated via depositions of one or more materials in a plurality of overlaying and adhered layers. Selectivity of deposition is obtained via a multi-cell controllable mask. Alternatively, net selective deposition is obtained via a blanket deposition and a selective removal of material via a multi-cell mask. Individual cells of the mask may contain electrodes comprising depositable material or electrodes capable of receiving etched material from a substrate. Alternatively, individual cells may include passages that allow or inhibit ion flow between a substrate and an external electrode and that include electrodes or other control elements that can be used to selectively allow or inhibit ion flow and thus inhibit significant deposition or etching.

U.S. Patent Application No. 60/429,484, filed on November 26, 2002, and entitled "Non-Conformable Masks and Methods and Apparatus for Forming Three-Dimensional Structures" is generally directed to electrochemical fabrication used to form multilayer structures (e.g. devices) from a plurality of overlaying and adhered layers. Masks, that are independent of a substrate to be operated on, are generally used to achieve selective patterning. These masks may allow selective deposition of material onto the substrate or they may allow selective etching of a substrate where after the created voids may be filled with a selected material that may be planarized to yield in effect a selective deposition of the selected material. The mask may be used in a contact mode or in a proximity mode. In the contact mode the mask and substrate physically mate to form substantially independent process pockets. In the proximity mode, the mask and substrate are positioned sufficiently close to allow formation of reasonably independent process pockets. In some embodiments, masks may have conformable contact surfaces (i.e. surfaces with sufficient

deformability that they can substantially conform to surface of the substrate to form a seal with it) or they may have semi-rigid or even rigid surfaces. Post deposition etching operations may be performed to remove flash deposits (thin undesired deposits).

- 5 U.S. Patent Application No. 10/309,521, filed on December 3, 2002, and entitled "Miniature RF and Microwave Components and Methods for Fabricating Such Components" is generally directed to RF and microwave radiation directing or controlling components provided that may be monolithic, that may be formed from a plurality of electrodeposition operations and/or from a plurality of deposited layers of
- 10 material, that may include switches, inductors, antennae, transmission lines, filters, and/or other active or passive components. Components may include non-radiation-entry and non-radiation-exit channels that are useful in separating sacrificial materials from structural materials. Preferred formation processes use electrochemical fabrication techniques (e.g. including selective depositions, bulk
- 15 depositions, etching operations and planarization operations) and post-deposition processes (e.g. selective etching operations and/or back filling operations).

- U.S. Patent Application No. XX/XXX,XXX, (Corresponding to MEMGen Docket No. P-US049-A-MG), filed on May 7, 2003, and entitled "Method for Fabricating Three-Dimensional Structures Including Surface Treatment of a First
- 20 Material in Preparation for Deposition of a Second Material" is generally directed to a method of fabricating three-dimensional structures from a plurality of adhered layers of at least a first and a second material wherein the first material is a conductive material and wherein each of a plurality of layers includes treating a surface of a first material prior to deposition of the second material. The treatment of the surface of
- 25 the first material either (1) decreases the susceptibility of deposition of the second material onto the surface of the first material or (2) eases or quickens the removal of any second material deposited on the treated surface of the first material. In some embodiments the treatment of the first surface includes forming a dielectric coating over the surface while the deposition of the second material occurs by an
- 30 electrodeposition process (e.g. an electroplating or electrophoretic process).

U.S. Patent Application No. 10/387,958, filed on March 13, 2003, and entitled "Electrochemical Fabrication Method and Apparatus for Producing Three-Dimensional Structures Having Improved Surface Finish" is generally directed to an electrochemical fabrication process that produces three-dimensional structures (e.g.

components or devices) from a plurality of layers of deposited materials wherein the formation of at least some portions of some layers are produced by operations that remove material or condition selected surfaces of a deposited material. In some embodiments, removal or conditioning operations are varied between layers or
5 between different portions of a layer such that different surface qualities are obtained. In other embodiments varying surface quality may be obtained without varying removal or conditioning operations but instead by relying on differential interaction between removal or conditioning operations and different materials encountered by these operations.

- 10 U.S. Patent Application No. XX/XXX,XXX, (Corresponding to MEMGen Docket No. P-US059-A-SC), filed on May 7, 2003, and entitled "Conformable Contact Masking Methods and Apparatus Utilizing In Situ Cathodic Activation of a Substrate" is generally directed to a electroplating processes (e.g. conformable contact mask plating and electrochemical fabrication processes) that includes in situ
15 activation of a surface onto which a deposit will be made are described. At least one material to be deposited has an effective deposition voltage that is higher than an open circuit voltage, and wherein a deposition control parameter is capable of being set to such a value that a voltage can be controlled to a value between the effective deposition voltage and the open circuit voltage such that no significant deposition
20 occurs but such that surface activation of at least a portion of the substrate can occur. After making electrical contact between an anode, that comprises the at least one material, and the substrate via a plating solution, applying a voltage or current to activate the surface without any significant deposition occurring, and thereafter without breaking the electrical contact, causing deposition to occur.

- 25 U.S. Patent Application No. XX/XXX,XXX, (Corresponding to MEMGen Docket No. P-US060-A-SC), filed on May 7, 2003, and entitled "Electrochemical Fabrication Methods With Enhanced Post Deposition Processing" is generally directed to a electrochemical fabrication process for producing three-dimensional structures from a plurality of adhered layers is provided where each layer comprises
30 at least one structural material (e.g. nickel) and at least one sacrificial material (e.g. copper) that will be etched away from the structural material after the formation of all layers have been completed. A copper etchant containing chlorite (e.g. Enthone C-38) is combined with a corrosion inhibitor (e.g. sodium nitrate) to prevent pitting of the structural material during removal of the sacrificial material. A simple process for

drying the etched structure without the drying process causing surfaces to stick together includes immersion of the structure in water after etching and then immersion in alcohol and then placing the structure in an oven for drying.

- U.S. Patent Application No. XX/XXX,XXX, (Corresponding to MEMGen
- 5 Docket No. P-US061-A-MG), filed on May 7, 2003, and entitled "Method of and Apparatus for Forming Three-Dimensional Structures Integral With Semiconductor Based Circuitry" is generally directed to an enhanced electrochemical fabrication processes that can form three-dimensional multi-layer structures using semiconductor based circuitry as a substrate. Electrically functional portions of the
- 10 structure are formed from structural material (e.g. nickel) that adheres to contact pads of the circuit. Aluminum contact pads and silicon structures are protected from copper diffusion damage by application of appropriate barrier layers. In some embodiments, nickel is applied to the aluminum contact pads via solder bump formation techniques using electroless nickel plating. In other embodiments,
- 15 selective electroless copper plating or direct metallization is used to plate sacrificial material directly onto dielectric passivation layers. In still other embodiments, structural material deposition locations are shielded, then sacrificial material is deposited, the shielding is removed, and then structural material is deposited.

- U.S. Patent Application No. XX/XXX,XXX, (Corresponding to MEMGen
- 20 Docket No. P-US064-A-MG), filed on May 7, 2003, and entitled "Methods of and Apparatus for Molding Structures Using Sacrificial Metal Patterns" is generally directed to molded structures, methods of and apparatus for producing the molded structures. At least a portion of the surface features for the molds are formed from multilayer electrochemically fabricated structures (e.g. fabricated by the EFAB™
- 25 formation process), and typically contain features having resolutions within the 1 to 100 μm range. The layered structure is combined with other mold components, as necessary, and a molding material is injected into the mold and hardened. The layered structure is removed (e.g. by etching) along with any other mold components to yield the molded article. In some embodiments portions of the layered structure
- 30 remain in the molded article and in other embodiments an additional molding material is added after a partial or complete removal of the layered structure.

U.S. Patent Application No. XX/XXX,XXX, (Corresponding to MEMGen Docket No. P-US065-A-MG), filed on May 7, 2003, and entitled "Electrochemically Fabricated Structures Having Dielectric or Active Bases and Methods of and

Apparatus for Producing Such Structures" is generally directed to multilayer structures that are electrochemically fabricated on a temporary (e.g. conductive) substrate and are thereafter bonded to a permanent (e.g. dielectric, patterned, multi-material, or otherwise functional) substrate and removed from the temporary substrate. In some embodiments, the structures are formed from top layer to bottom layer, such that the bottom layer of the structure becomes adhered to the permanent substrate, while in other embodiments the structures are formed from bottom layer to top layer and then a double substrate swap occurs. The permanent substrate may be a solid that is bonded (e.g. by an adhesive) to the layered structure or it may start out as a flowable material that is solidified adjacent to or partially surrounding a portion of the structure with bonding occurring during solidification. The multilayer structure may be released from a sacrificial material prior to attaching the permanent substrate or it may be released after attachment.

U.S. Patent Application No. XX/XXX,XXX, (Corresponding to MEMGen Docket No. P-US067-A-MG), filed on May 7, 2003, and entitled "Multistep Release Method for Electrochemically Fabricated Structures" is generally directed to multilayer structures that are electrochemically fabricated from at least one structural material (e.g. nickel), that is configured to define a desired structure and which may be attached to a substrate, and from at least one sacrificial material (e.g. copper) that surrounds the desired structure. After structure formation, the sacrificial material is removed by a multi-stage etching operation. In some embodiments sacrificial material to be removed may be located within passages or the like on a substrate or within an add-on component. The multi-stage etching operations may be separated by intermediate post processing activities, they may be separated by cleaning operations, or barrier material removal operations, or the like. Barriers may be fixed in position by contact with structural material or with a substrate or they may be solely fixed in position by sacrificial material and are thus free to be removed after all retaining sacrificial material is etched.

U.S. Patent Application No. XX/XXX,XXX, (Corresponding to MEMGen Docket No. P-US068-A-MG), filed on May 7, 2003, and entitled "Methods of and Apparatus for Electrochemically Fabricating Structures Via Interlaced Layers or Via Selective Etching and Filling of Voids" is generally directed to multi-layer structures that are electrochemically fabricated by depositing a first material, selectively etching the first material (e.g. via a mask), depositing a second material to fill in the voids

created by the etching, and then planarizing the depositions so as to bound the layer being created and thereafter adding additional layers to previously formed layers.

The first and second depositions may be of the blanket or selective type. The repetition of the formation process for forming successive layers may be repeated

- 5 with or without variations (e.g. variations in: patterns; numbers or existence of or parameters associated with depositions, etchings, and or planarization operations; the order of operations, or the materials deposited). Other embodiments form multi-layer structures using operations that interface material deposited in association with some layers with material deposited in association with other layers.

- 10 Various other embodiments of the present invention exist. Some of these embodiments may be based on a combination of the teachings herein with various teachings incorporated herein by reference. Some embodiments may not use any blanket deposition process and/or they may not use a planarization process. Some embodiments may involve the selective deposition of a plurality of different materials
- 15 on a single layer or on different layers. Some embodiments may use blanket depositions processes that are not electrodeposition processes. Some embodiments may use selective deposition processes that are not contact masking processes and are not even electrodeposition processes. Some embodiments may use nickel as a structural material while other embodiments may use different
- 20 materials such as gold, silver, or any other electrodepositable materials that can be separated from the copper and/or some other sacrificial material. Some embodiments may use copper as the structural material with or without a sacrificial material. Some embodiments may remove a sacrificial material while other embodiments may not. In some embodiments the anode may be different from a
- 25 contact mask support and the support may be a porous structure or other perforated structure. Some embodiments may use multiple conformable contact masks with different patterns so as to deposit different selective patterns of material on different layers and/or on different portions of a single layer. In some embodiments, the depth of deposition will be enhanced by pulling the conformable contact mask away from
- 30 the substrate as deposition is occurring in a manner that allows the seal between the conformable portion of the CC mask and the substrate to shift from the face of the conformal material to the inside edges of the conformable material.

In view of the teachings herein, many further embodiments, alternatives in design and uses of the invention will be apparent to those of skill in the art. As such,

it is not intended that the invention be limited to the particular illustrative embodiments, alternatives, and uses described above but instead that it be solely limited by the claims presented hereafter.

We Claim:

1. An electrochemical fabrication process for producing a three-dimensional structure from a plurality of adhered layers, the process comprising:

- (A) depositing at least a portion of a layer onto the substrate,
5 wherein the substrate may comprise previously deposited material; and
(B) forming a plurality of layers such that each successive layer is formed adjacent to and adhered to a previously deposited layer;
wherein the layers comprise at least three different materials and wherein the layers contain patterns of material comprising:
10 (1) a desired structural component that is to be protected and that is formed from at least one structural material;
(2) a protective enclosure that is formed at least in part from a structural material, wherein at least one portion of the enclosure at least partially surrounds the desired structural component, and wherein the
15 enclosure is limited by at least one opening therein;
(3) a sealing material located near the at least one opening;
and
(4) a sacrificial material located at least partially between the desired structural component to be protected and at least a portion of the
20 enclosure;
wherein after formation of the layers at least portion of the sacrificial material located between the desired structural component and at least a portion of the enclosure is removed; and
wherein after the removal of the sacrificial material, the sealing material
25 is made to temporarily flow and seal at least one opening to block or significantly limit a passage of material from an outside of the enclosure to an inside of the enclosure via the at least one sealed opening.

2. The process of claim 1 wherein the removal of the sacrificial material
30 comprises etching.

3. The process of claim 1 wherein after removal and prior to sealing, a reducing agent is provided at least one location within or near the at least one opening to reduce the presence of any oxides at the at least one location.

4. The process of claim 1 wherein after removal and prior to sealing, a desired fill gas is made to fill an interior cavity of the enclosure in which the desired structural component is at least partially located.

5

5. The process of claim 1 wherein after removal and prior to sealing, an interior cavity of the enclosure in which the desired structural component is at least partially located is at least partially evacuated.

10

6. The process of claim 1 wherein at least one opening and the sealing material are so located that the sealing material need not flow over any structural material when flowing to seal the opening.

7. The process of claim 1 wherein at least one opening is sealed at least
15 in part by the surface tension of the flowable sealing material causing the sealing material to bulge and bridge the opening.

8. The process of claim 1 wherein at least one opening has sloped walls that give the opening a non-fixed cross-sectional dimension through the enclosure,
20 the sealing material, or a combination of the sealing material and the enclosure.

9. The process of claim 1 wherein at least one opening has a restriction around which sealing material will flow when sealing the opening.

25

10. An electrochemical fabrication process for producing a three-dimensional structure from a plurality of adhered layers, the process comprising:

(A) depositing at least a portion of a layer onto a substrate, wherein the substrate may comprise previously deposited material; and

(B) forming a plurality of layers such that each successive layer
30 formed adjacent to and adhered to a previously deposited layer

wherein the layers comprise at least two different materials and wherein the layers contain patterns of material comprising:

(1) a desired structural component that is to be protected and that is formed from at least one structural material;

(2) a protective enclosure that is formed at least in part from a structural material, wherein at least one portion of the enclosure at least partially surrounds the desired structural component, and wherein the enclosure is limited by at least one opening therein;

(3) a sacrificial material located at least partially between the desired structural component to be protected and at least a portion of the enclosure;

wherein after formation of the layers at least portion of the sacrificial material located between the desired structural component and at least a portion of the enclosure is removed; and

wherein after the removal of the sacrificial material, a seal is formed between the protective enclosure and a sealing structure wherein at least one of the protective enclosure or sealing structure comprises a sealing material that may be used in establishing a sealing of the at least one opening to block or significantly limit a passage of material from an outside of the enclosure to an inside of the enclosure via the at least one sealed opening.

11. An electrochemical fabrication process for producing a three-dimensional structure from a plurality of adhered layers, the process comprising:

(A) depositing at least a portion of a layer onto a substrate, wherein the substrate may comprise previously deposited material; and

(B) forming a plurality of layers such that each successive layer is formed adjacent to and adhered to a previously deposited layer

wherein the layers comprise at least two different materials and

wherein the layers contain patterns of material comprising

(1) a desired structural component that is to be protected and that is formed from at least one structural material;

(2) a protective enclosure that is formed at least in part from a structural material, wherein at least one portion of the enclosure at least partially surrounds the desired structural component, and wherein the enclosure is limited by at least one opening therein;

(3) at least one blocking structure located along a line of sight that includes the at least one opening but spaced from the protective enclosure; and

(4) a sacrificial material located at least partially between the desired structural component to be protected and at least a portion of the enclosure;

wherein after formation of the layers at least portion of the sacrificial material located between the desired structural component and at least a portion of the enclosure is removed; and

wherein after the removal of the sacrificial material, a sealing material is deposited such that it strikes said blocking material which inhibits the sealing material from entering the enclosure in bulk, where by continued build up of the sealing material seals the at least one opening to block or significantly limit a passage of material from an outside of the enclosure to an inside of the enclosure via the at least one sealed opening.

12. An electrochemical fabrication process for producing a three-dimensional structure from a plurality of adhered layers, the process comprising:

(A) depositing at least a portion of a layer onto a substrate, wherein the substrate may comprise previously deposited material; and

(B) forming a plurality of layers such that each successive layer is formed adjacent to and adhered to a previously deposited layer

wherein the layers comprise at least two different materials and wherein the layers contain patterns of material comprising:

(1) a desired structural component that is to be protected and that is formed from at least one structural material;

(2) a protective enclosure that is formed at least in part from a structural material, wherein at least one portion of the enclosure at least partially surrounds the desired structural component, and wherein the enclosure is limited by at least one opening therein; and

(3) a sacrificial material located at least partially between the desired structural component to be protected and at least a portion of the enclosure.

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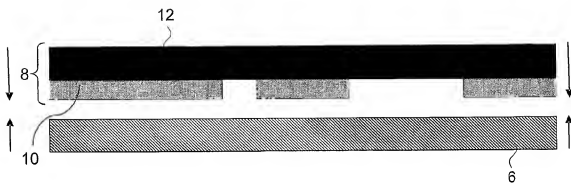


Figure 1(a)

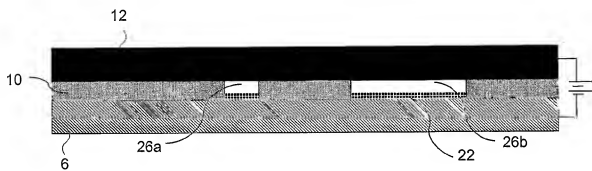


Figure 1(b)

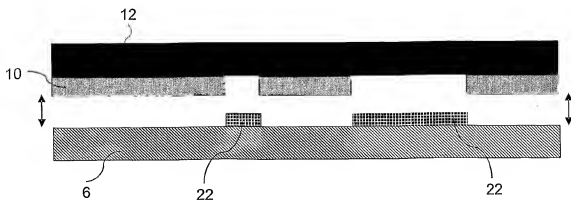


Figure 1(c)

2/22

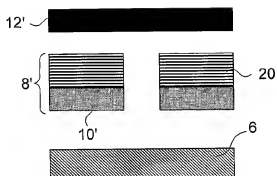


Figure 1(d)

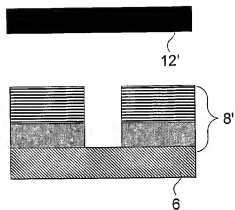


Figure 1(e)

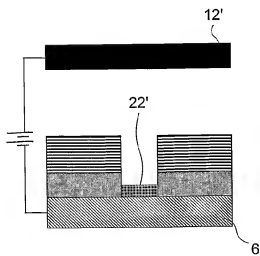


Figure 1(f)

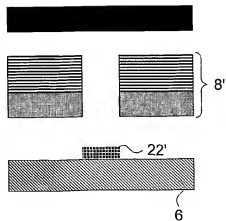


Figure 1(g)

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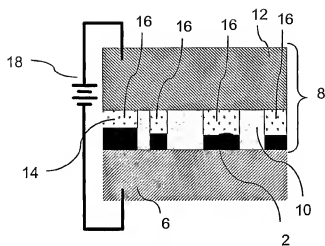


Figure 2(a)

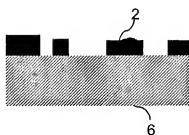


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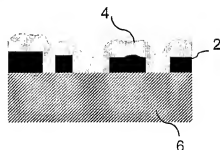


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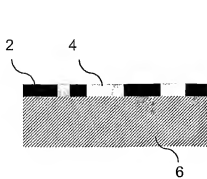


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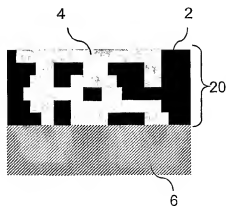
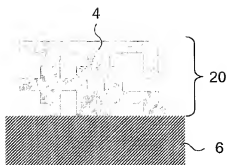
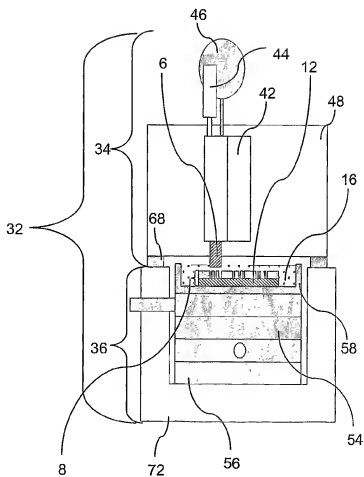


Figure 2(e)

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**Figure 2(f)****Figure 3(a)**

5/22

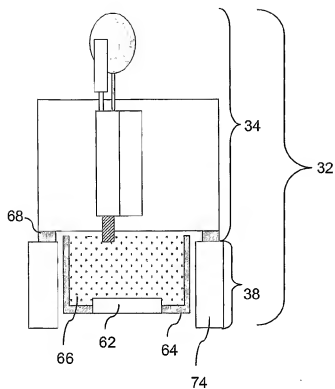


Figure 3(b)

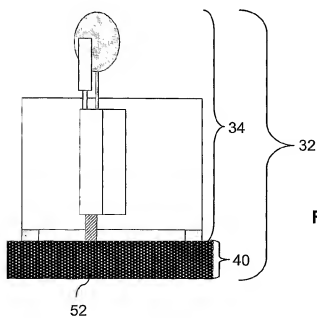


Figure 3(c)

6/22

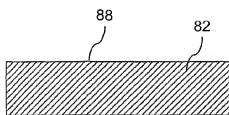


Figure 4(a)

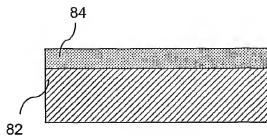


Figure 4(b)

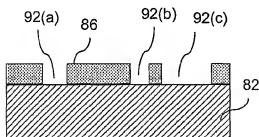


Figure 4(c)

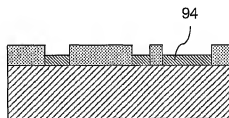


Figure 4(d)

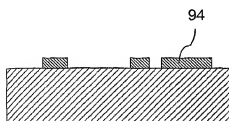


Figure 4(e)

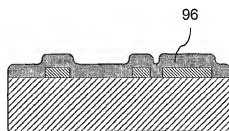


Figure 4(f)

7/22

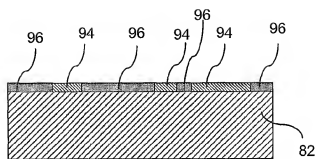


Figure 4(g)

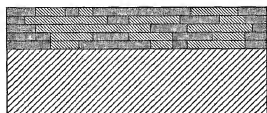


Figure 4(h)



Figure 4(i)

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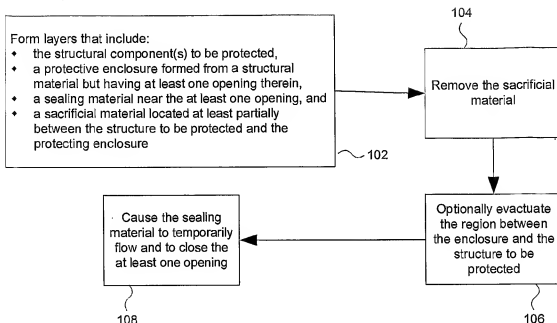


Figure 5(a)

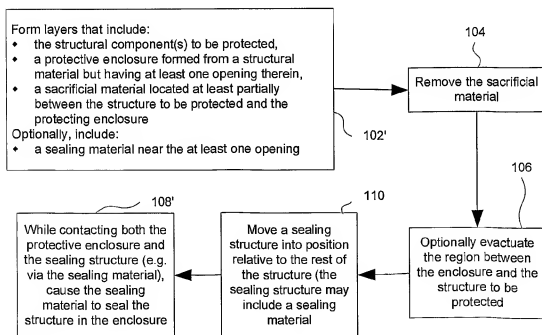


Figure 5(b)

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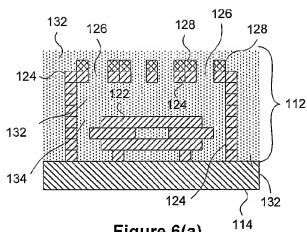


Figure 6(a)

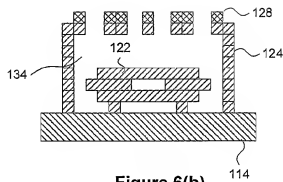


Figure 6(b)

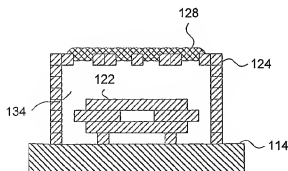


Figure 6(c)

X

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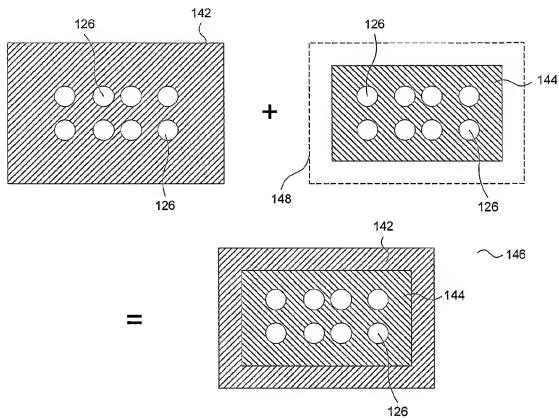


Figure 6(d)

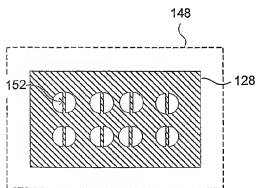


Figure 7(a)

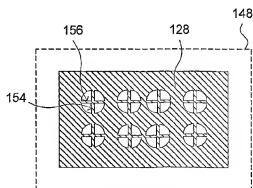


Figure 7(b)

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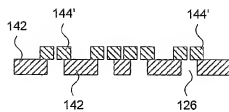


Figure 7 (a)

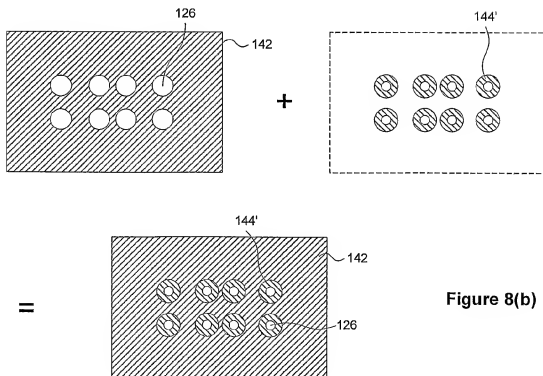


Figure 8(b)

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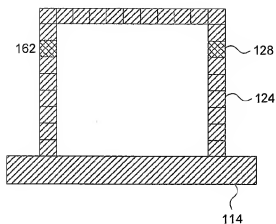


Figure 9(a)

Figure 9(b)

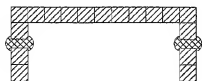
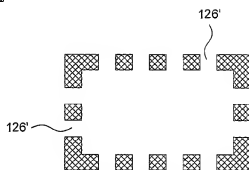
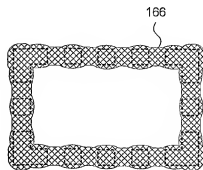


Figure 9(c)

Figure 9(d)



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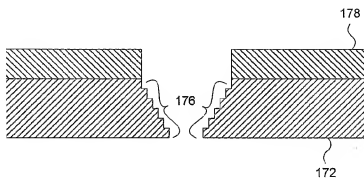


Figure 10(a)

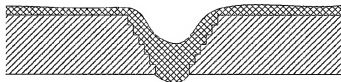


Figure 10(b)

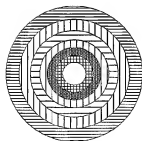


Figure 10(c)

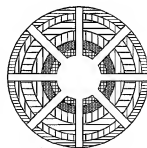


Figure 10(d)

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Figure 10(e)

Figure 10(f)

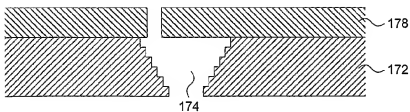
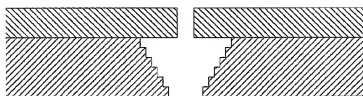
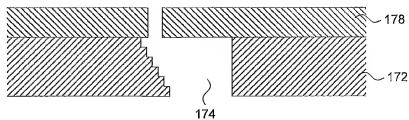


Figure 10(g)

Figure 10(h)



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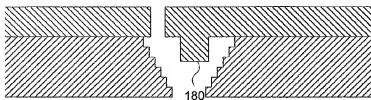


Figure 10(i)

Figure 11(a)

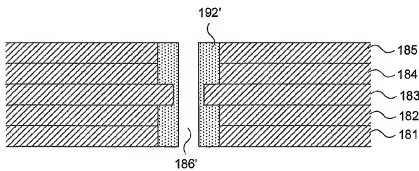
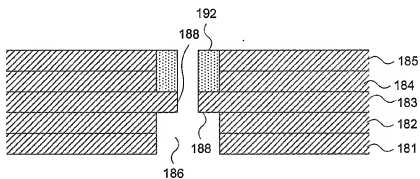
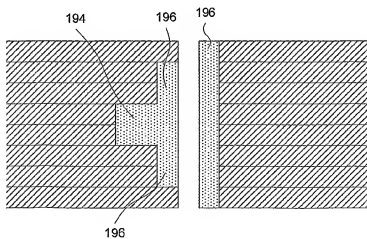


Figure 11(b)

Figure 11(c)



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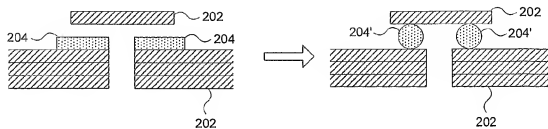


Figure 12(a)

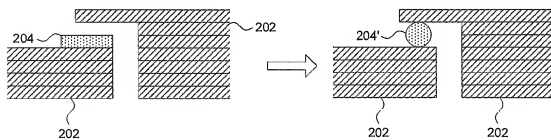


Figure 12(b)

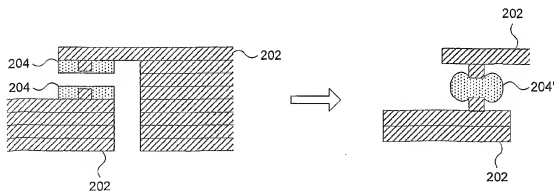
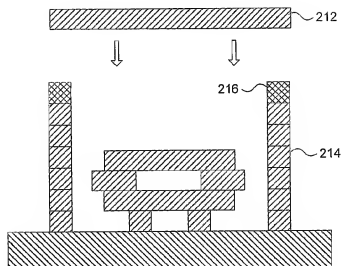
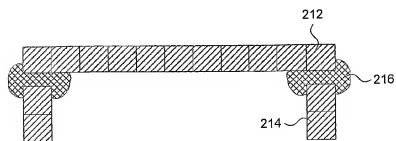


Figure 12(c)

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**Figure 13(a)****Figure 13(b)**

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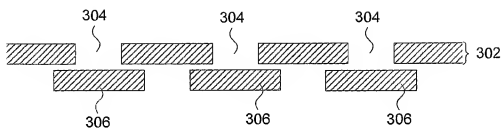


Figure 14(a)

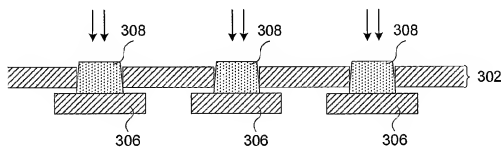


Figure 14(b)

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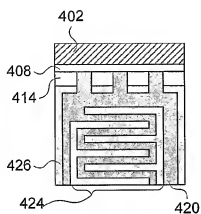


Figure 15(a)

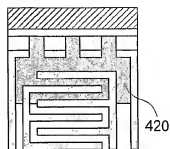


Figure 15(b)

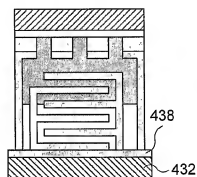


Figure 15(c)

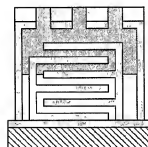


Figure 15(d)

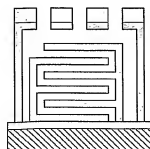


Figure 15(e)

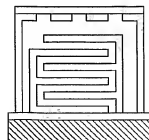


Figure 15(f)

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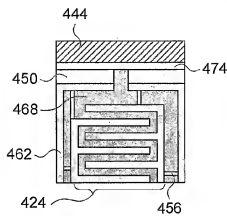


Figure 16(a)

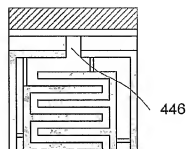


Figure 16(b)

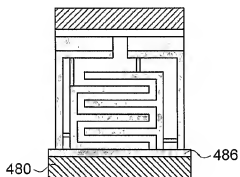


Figure 16(c)

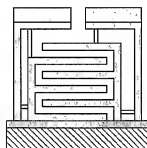


Figure 16(d)

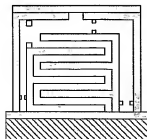


Figure 16(e)

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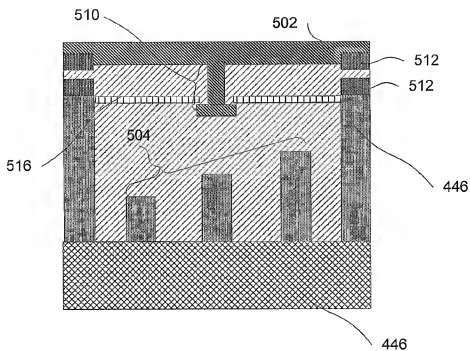


Figure 17(a)

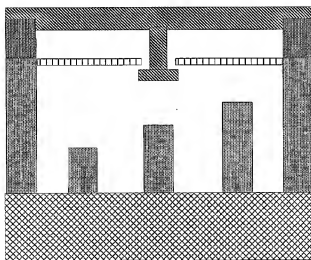


Figure 17(b)

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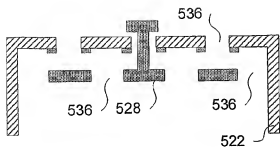


Figure 18(a)

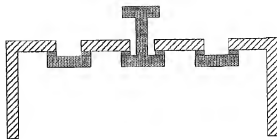


Figure 18(b)

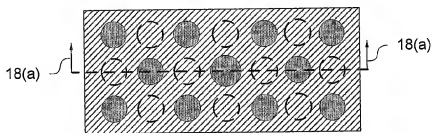


Figure 18(c)

